

Atty. Docket No. PIA31191/ANS/US

## IN THE UNITED STATES PATENT &amp; TRADEMARK OFFICE

IN RE APPLICATION OF:

Kwan Ju Koh

APPLICATION NO: 10/765,027

FILED: January 26, 2004

FOR: **METHODS OF  
MANUFACTURING MOSFET  
DEVICES**

PATENT NO.: 7,192,837

**ISSUED: March 20, 2007**

I hereby certify that this document is being transmitted to the USPTO or deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on June 25, 2009.

By: /Judy Ryan/  
Judy Ryan

## REQUEST FOR A CERTIFICATE OF CORRECTION UNDER 37 CFR 1.322

ATTENTION: Certificate of Correction Branch  
COMMISSIONER FOR PATENTS  
OFFICE OF PATENT PUBLICATION  
P.O. BOX 1450  
ALEXANDRIA, VA 22313-1450  
FAX: (571) 273-8300

SIR:

Applicants respectfully request a Certificate of Correction in the above-referenced patent.

The facts are as follows:

Typographical errors appear in the above referenced patent as issued that resulted from errors by the U.S. Patent and Trademark Office. Applicants respectfully request a Certificate of Correction to correct the typographical errors. No new matter or new issues requiring further examination are introduced by the requested corrections.

Column 2, line 46 of the issued patent recites: "farming a first oxide layer". Applicant requests that the statement be corrected to state: "forming a first oxide layer".

Column 2, line 54 of the issued patent recites: "including the tightly doped drain". Applicant requests that the statement be corrected to state: "including the lightly doped drain".

Column 2, line 57 of the issued patent recites: "forming a second oxide layer aver an exposed portion". Applicant requests that the statement be corrected to state: "forming a second oxide layer over an exposed portion".

Column 2, line 62 of the issued patent recites: "first aid do layer". Applicants request that the statement be corrected to state: "first oxide layer".

Column 3, lines 24-25 of the issued patent recites: "etching to exposed substrate". Applicants request that the statement be corrected to state: "etching the exposed substrate".

Column 3, line 31 of the issued patent recites: "removing to first nitride layer". Applicants request that the statement be corrected to state: "removing the first nitride layer".

Column 3, line 32 of the issued patent recites: "to polysilicon layer". Applicants request that the statement be corrected to state: "the polysilicon layer".

**The corrections requested are as follows:**

Column 2, line 46 of the issued patent: change "farming a first oxide layer" to --forming a first oxide layer--.

Column 2, line 54 of the issued patent: change "including the tightly doped drain" to --including the lightly doped drain--.

Column 2, line 57 of the issued patent: change "forming a second oxide layer aver an exposed portion" to --forming a second oxide layer over an exposed portion--.

Column 2, line 62 of the issued patent: change "first aid do layer" to --first oxide layer--.

Column 3, lines 24-25 of the issued patent: change "etching to exposed substrate" to --etching the exposed substrate--.

Column 3, line 31 of the issued patent: change "removing to first nitride layer" to --removing the first nitride layer--.

Column 3, line 32 of the issued patent: change "to polysilicon layer" to --the polysilicon layer--.

Any additional information and/or assistance with this Request may be obtained from the undersigned practitioner.

Respectfully submitted,

/William K. Nelson/

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## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

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PATENT NO. : 7,192,837  
APPLICATION NO.: 10/765,027  
ISSUE DATE : March 20, 2007  
INVENTOR(S) : Kwan Ju Koh

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

### IN THE CLAIMS

Column 2, line 46 of the issued patent: change "farming a first oxide layer" to --forming a first oxide layer--.

Column 2, line 54 of the issued patent: change "including the tightly doped drain" to --including the lightly doped drain--.

Column 2, line 57 of the issued patent: change "second oxide layer aver an exposed portion" to --second oxide layer over an exposed portion--.

Column 2, line 62 of the issued patent: change "first aid do layer" to --first oxide layer--.

Column 3, lines 24-25 of the issued patent: change "etching to exposed substrate" to --etching the exposed substrate--.

Column 3, line 31 of the issued patent: change "removing to first nitride layer" to --removing the first nitride layer--.

Column 3, line 32 of the issued patent: change "to polysilicon layer" to --the polysilicon layer--.

### MAILING ADDRESS OF SENDER (Please do not use customer number below):

The Law Offices of Andrew D. Fortney, Ph.D., P.C.  
401 W. Fallbrook Avenue, Suite 204  
Fresno, CA 93711

This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (i.e., GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
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9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.